CLAIMS

1. A composition for the removal of an organic photoresist and/or other materials from a substrate, which comprises:
aryl sulfonic acid or alkylaryl sulfonic acid or mixtures thereof;
1,3-dihydroxybenzene (resorcinol) or sorbitol or mixtures thereof; and
one or more hydrocarbon solvents having a flash point of greater than about 65ºC.

2. The composition of claim 1, further comprising water at less than about 3 % by weight based on the total weight of the composition.

3. The composition of claim 1 comprising greater than about 0.08 % by weight sulfuric acid.

4. The composition of claim 1 wherein said composition comprises said aryl sulfonic acid or said alkylaryl sulfonic acid or said mixtures thereof in an amount from 20 to 40 % by weight based on the total weight of the composition.

5. The composition of claim 1 wherein said composition comprises said 1,3-dihydroxybenzene or said sorbitol or said mixtures thereof from 0.2 to 3.5 weight percent based on the total weight of the composition.

6. The composition of claim 1 wherein said composition comprises said one or more hydrocarbon solvents in an amount from 60 to 85 percent by weight based on the total weight of the composition.

7. The composition of claim 2 wherein said composition comprises said water at a positive amount up to about 0.5 weight percent or less.

8. The composition of claim 3 wherein said composition comprises sulfuric acid in an amount from about 0.08 to less than 1 percent by weight based on the total weight of the composition.

9. The composition of claim 5 wherein said composition comprises said 1,3-dihydroxybenzene or said sorbitol or said mixtures thereof at an amount from 0.5 to 3.5 weight percent based on the total weight of the composition.

10. The composition of claim 9 wherein said composition comprises said aryl sulfonic acid or said alkylaryl sulfonic acid or said mixtures thereof in an amount from 22 to 38 % by weight based on the total weight of the composition.

11. The composition of claim 10 wherein said composition comprises said water at a positive amount up to about 0.5 weight percent or less based on the total weight of the composition.

12. The composition of claim 1 wherein said one or more hydrocarbon solvents have a flash point of from about 65ºC to 85ºC, or from about 90ºC to 100ºC.

13. The composition of claim 1 wherein said one or more hydrocarbon solvents are preferably refined from petroleum and said hydrocarbons comprise C8-C18 hydrocarbons at an amount greater than about 50% of total weight of said hydrocarbon solvents in said composition.

14. The composition of claim 1 wherein said one or more hydrocarbon solvents comprises greater than 50% of aliphatic containing hydrocarbons by weight of the total weight of the hydrocarbon solvents in said composition.

15. The composition of claim 1 wherein said one or more hydrocarbon solvents comprises greater than 50% of aromatic containing hydrocarbons by weight of the total weight of the hydrocarbon solvents in said composition.

16. The composition of claim 1 wherein said one or more hydrocarbon solvents comprises greater than 50% by weight paraffins.

17. The composition of claim 16 wherein said composition comprises water at a positive amount up to about 0.5 weight percent or less.

18. A method of stripping photoresist and/or other materials from a substrate, which comprises the steps of: providing the composition of claim 1 and contacting the photoresist with the composition at a temperature from 60 to 100ºC for from 5 to 120 minutes.

19. The method of claim 18 wherein the substrate is a silicon wafer having a silicon dioxide insulation layer metallized with one or more metals selected from aluminum, titanium, titanium tungsten, silver, nickel, nickel vanadium and copper.

20. The method of claim 19 wherein said method provides Al etch rates of 2 Å/min or less, Ni etch rates of 1 Å/min or less, or NiV etch rates of 3 Å/min or less.